



SANYO Semiconductors

## DATA SHEET

N-Channel Silicon MOSFET

# CPH6415 — General-Purpose Switching Device Applications

## Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 1.8V drive.

## Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		20	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		4	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	16	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (1200mm <sup>2</sup> ×0.8mm)	1.6	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	20			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>D</sub> =20V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>D</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>D</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>D</sub> =10V, I <sub>D</sub> =2A	3.8	5.5		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =2A, V <sub>GS</sub> =4V		48	63	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V		63	88	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =0.5A, V <sub>GS</sub> =1.8V		80	120	mΩ

Marking : KR

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# CPH6415

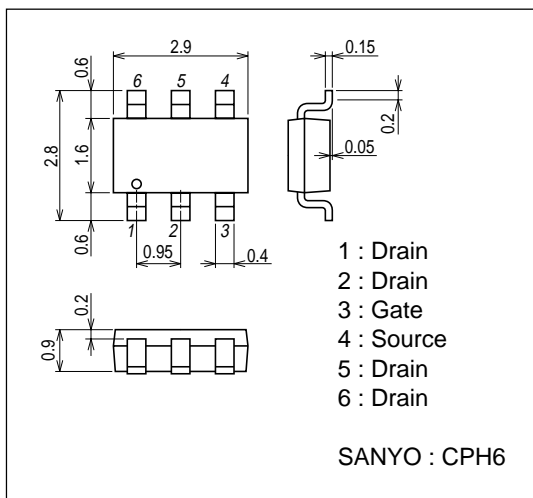
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	$V_{DS}=10V$ , $f=1MHz$		280		pF
Output Capacitance	Coss	$V_{DS}=10V$ , $f=1MHz$		60		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=10V$ , $f=1MHz$		38		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		13		ns
Rise Time	$t_r$	See specified Test Circuit.		50		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		33		ns
Fall Time	$t_f$	See specified Test Circuit.		30		ns
Total Gate Charge	Qg	$V_{DS}=10V$ , $V_{GS}=4V$ , $I_D=4A$		5.0		nC
Gate-to-Source Charge	Qgs	$V_{DS}=10V$ , $V_{GS}=4V$ , $I_D=4A$		0.85		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=10V$ , $V_{GS}=4V$ , $I_D=4A$		0.85		nC
Diode Forward Voltage	$V_{SD}$	$I_S=4A$ , $V_{GS}=0V$		0.88	1.2	V

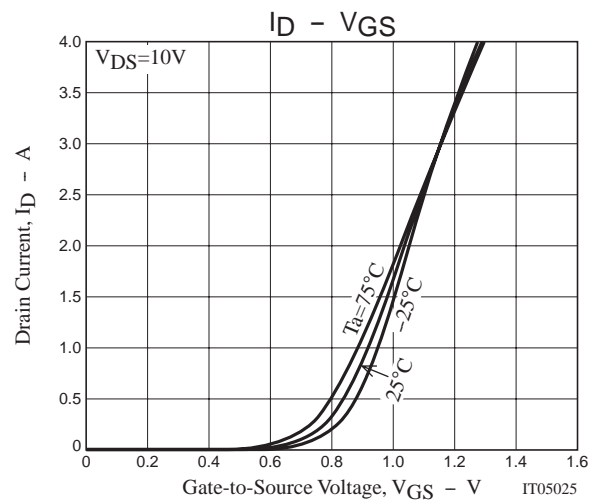
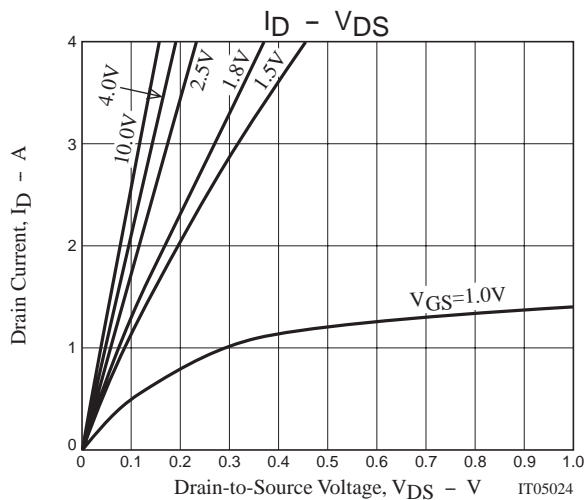
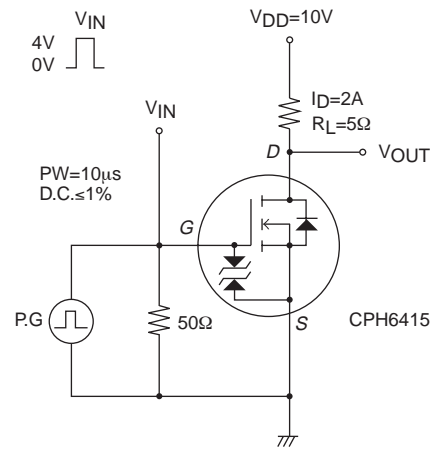
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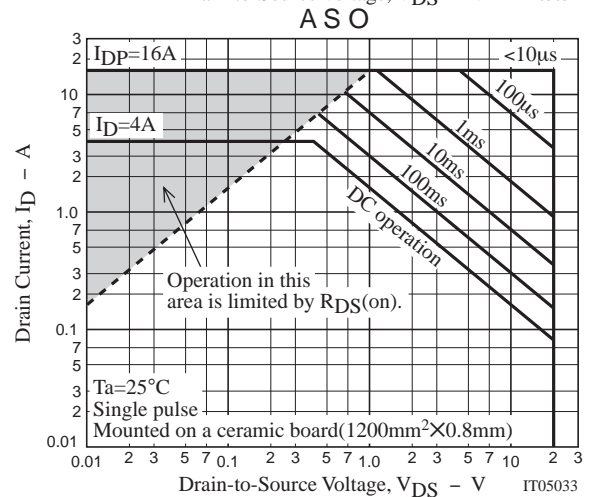
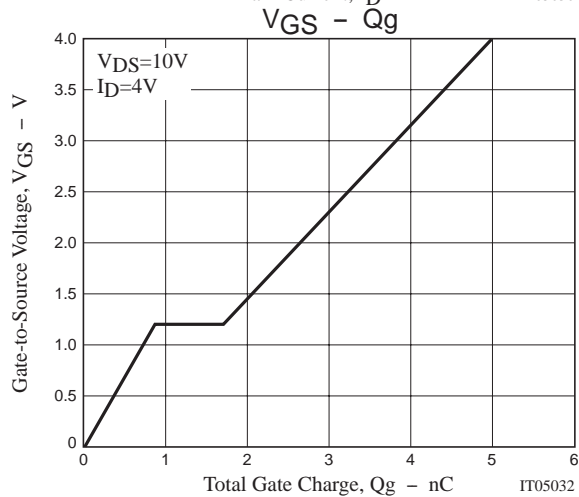
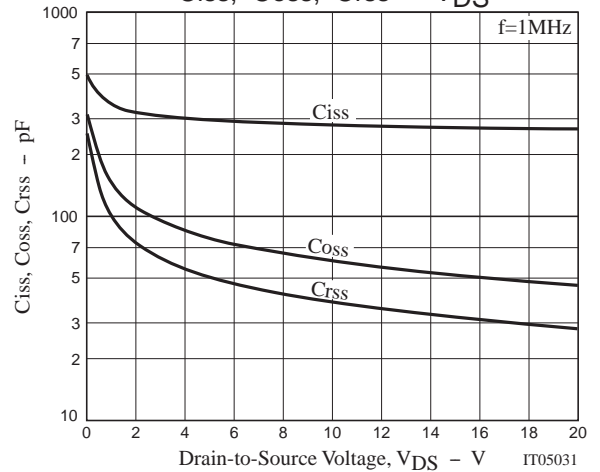
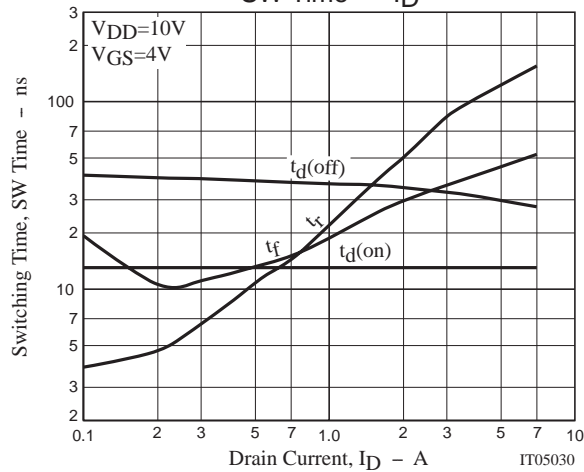
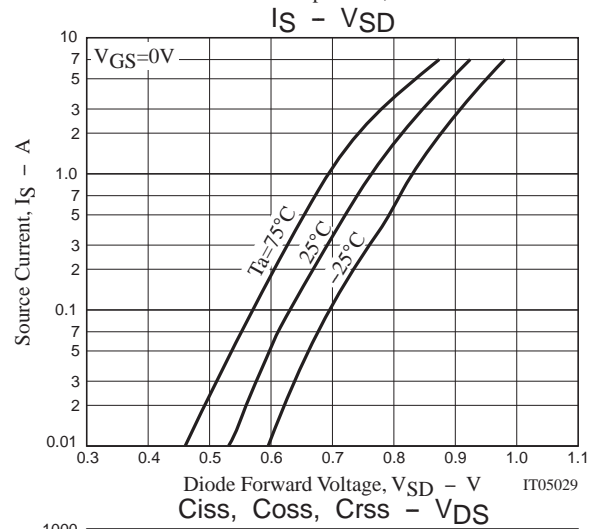
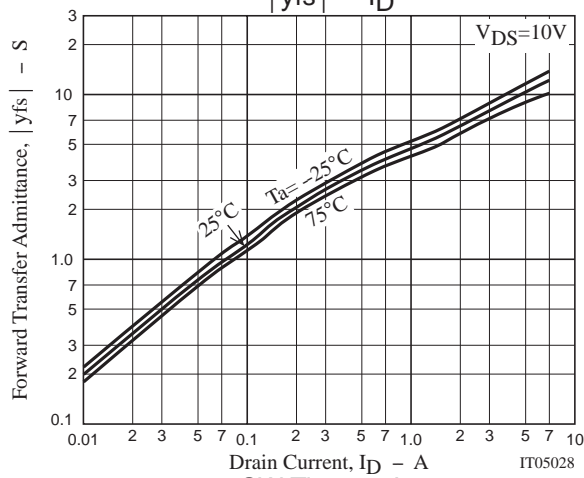
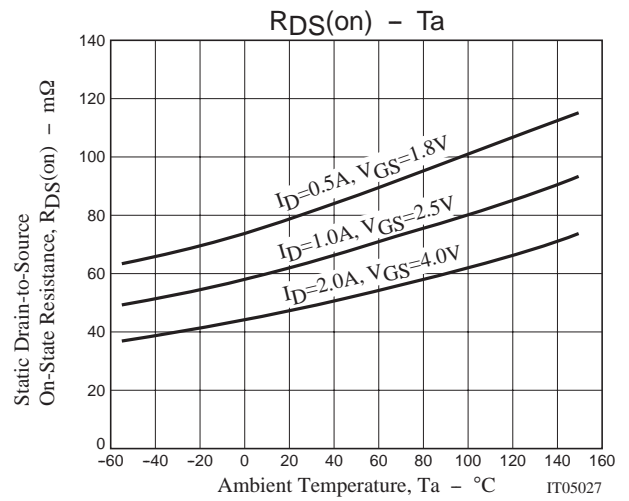
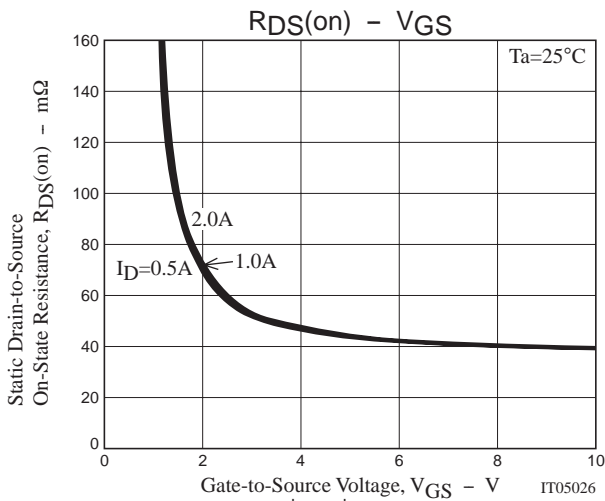
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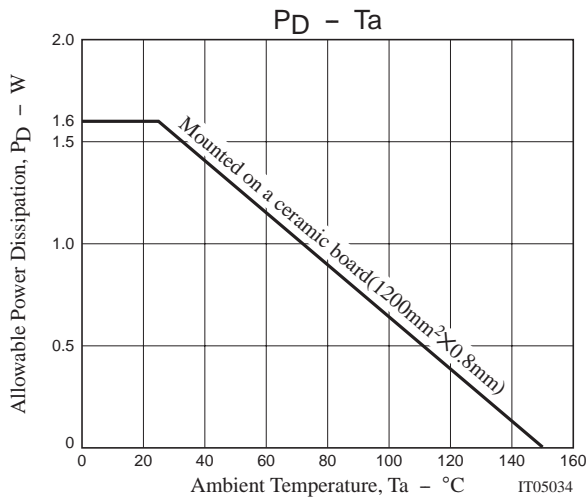
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## Switching Time Test Circuit







Note on usage : Since the CPH6415 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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